Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
60V	5Ω @ V_{GS} = 10V	0.21A
	6Ω @ V_{GS} = 5V	0.20A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features

- Low On-Resistance: $R_{DS(ON)}$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected up to 1kV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.**
  https://www.diodes.com/quality/product-definitions/

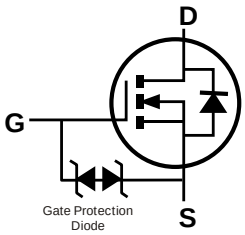
Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)

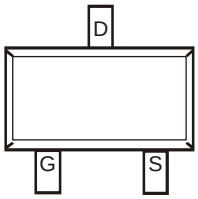
ESD Protected up to 1kV

SOT523

Top View



Equivalent Circuit



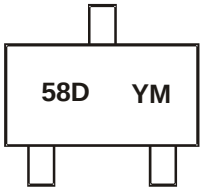
Top View
Pin Out Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN65D8LT-7	SOT523	3000/Tape & Reel
DMN65D8LT-13	SOT523	10000/Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



58D = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$= Year (ex: H = 2020)
M = Month (ex: 9 = September)

Date Code Key

Year	2014	…	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	B	…	G	H	I	J	K	L	M	N	O	P

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 5.0V	Steady State	T_A = +25°C	I_D	210	mA
		T_A = +70°C		170	
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	210	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	0.7	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	0.7	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	426	°C/W
Total Power Dissipation (Note 6)		P_D	360	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	351	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 10µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.2	—	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	2.0	5.0	Ω	V_{GS} = 10V, I_D = 0.115A
			2.2	6.0		V_{GS} = 5V, I_D = 0.115A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	24	—	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	2.8	—		
Reverse Transfer Capacitance	C_{rss}	—	1.8	—		
Gate Resistance	R_g	—	50	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	—	0.4	—	nC	V_{DD} = 30V, V_{GS} = 4.5V, I_D = 150mA
Gate-Source Charge	Q_{gs}	—	0.12	—		
Gate-Drain Charge	Q_{gd}	—	0.14	—		
Turn-On Delay Time	$t_{D(ON)}$	—	2.0	—	ns	V_{GS} = 10V, V_{DD} = 30V, R_g = 25Ω, I_D = 0.2A
Turn-On Rise Time	t_R	—	1.9	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	9.5	—		
Turn-Off Fall Time	t_F	—	4.3	—		

Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

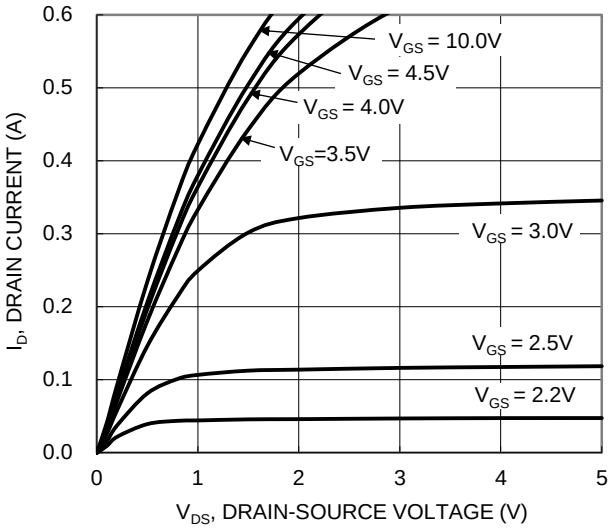


Figure 1. Typical Output Characteristic

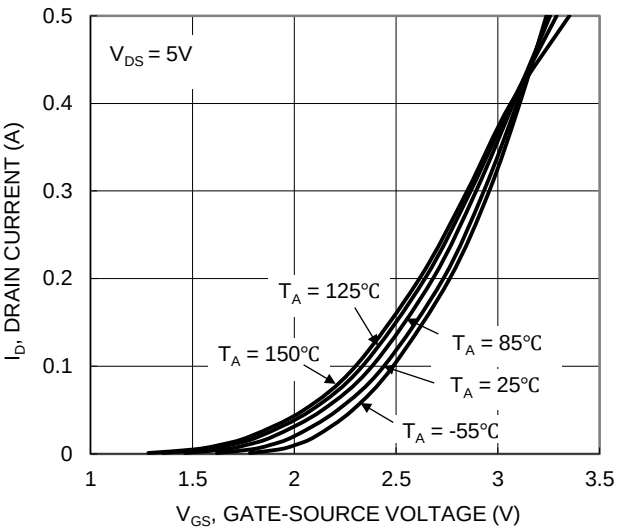


Figure 2. Typical Transfer Characteristic

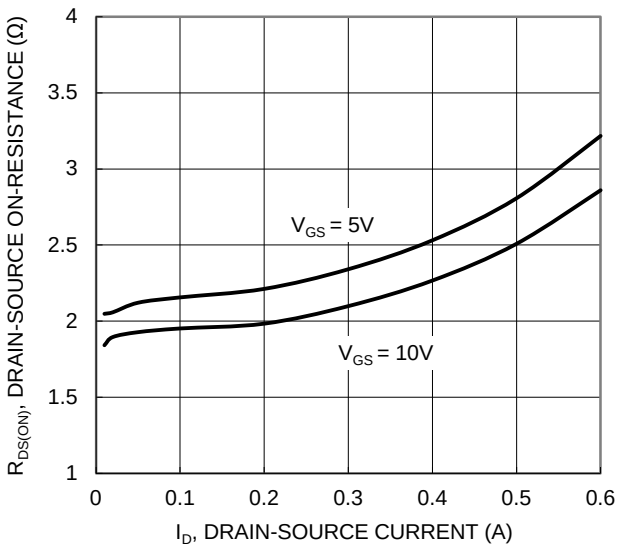


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

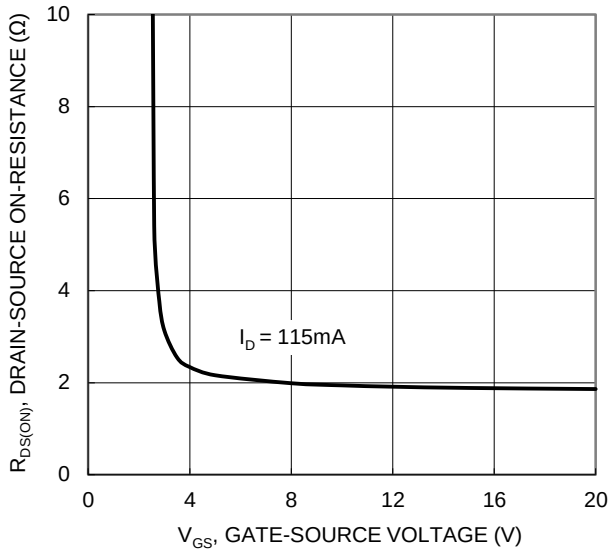


Figure 4. Typical Transfer Characteristic

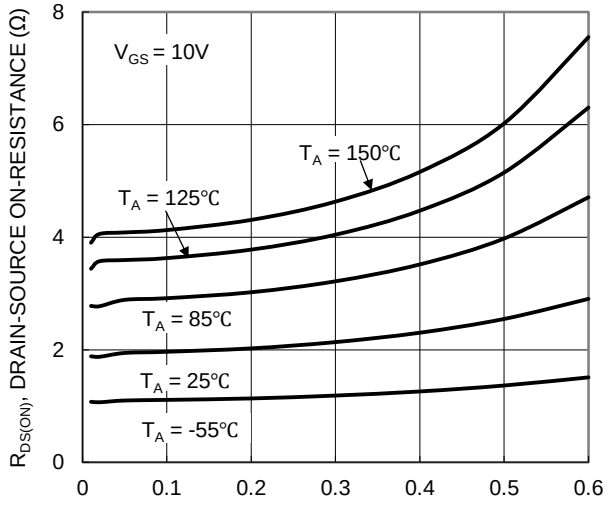


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

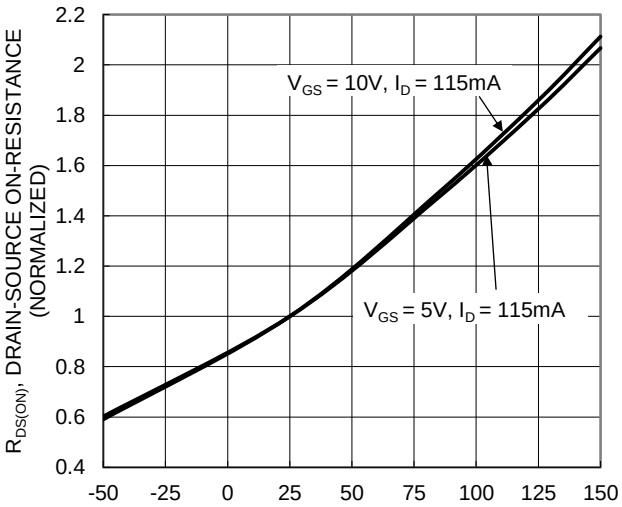


Figure 6. On-Resistance Variation with Junction Temperature

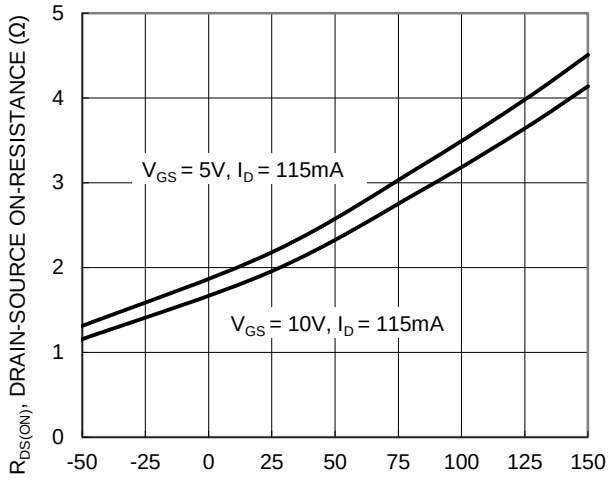


Figure 7. On-Resistance Variation with Junction Temperature

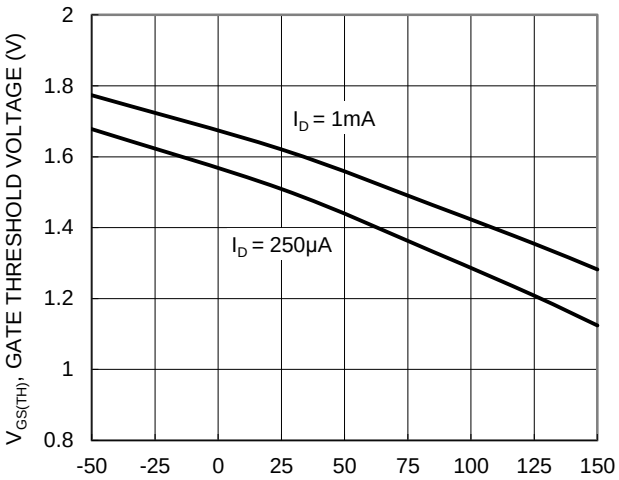


Figure 8. Gate Threshold Variation vs. Junction Temperature

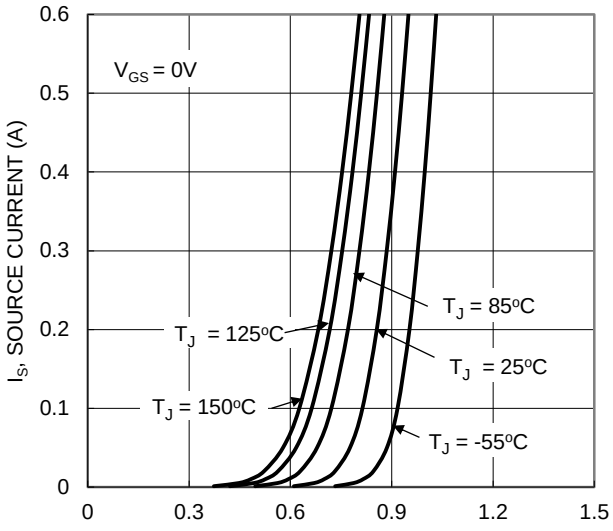


Figure 9. Diode Forward Voltage vs. Current

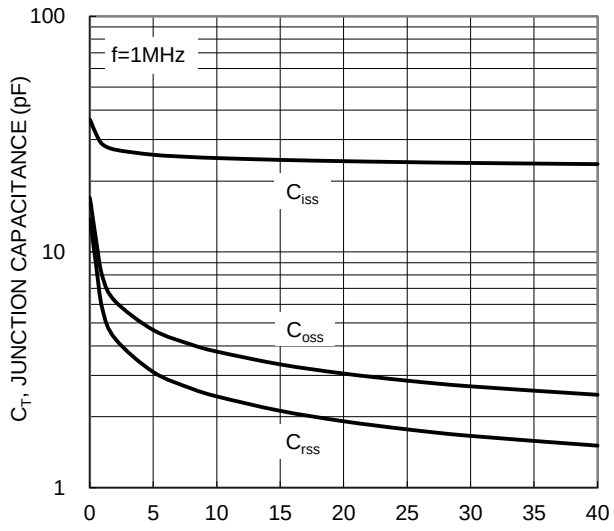


Figure 10. Typical Junction Capacitance

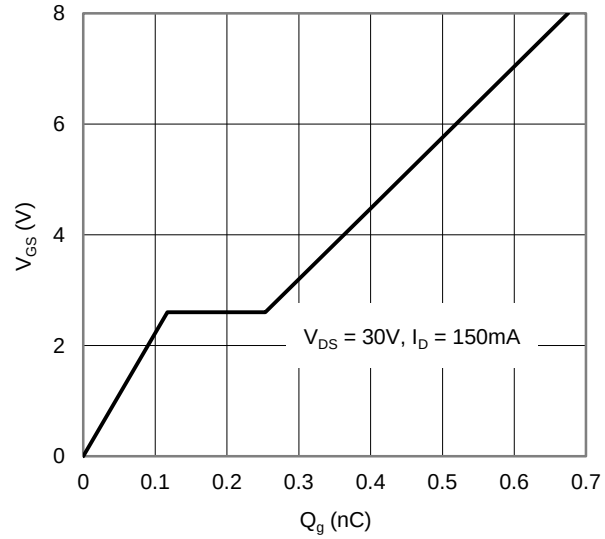


Figure 11. Gate Charge

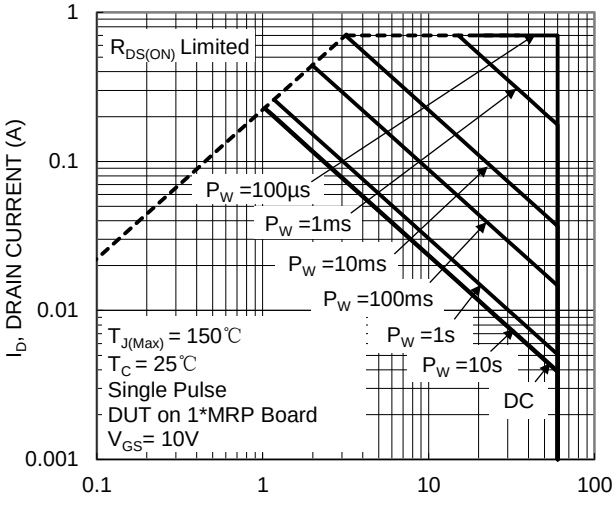


Figure 12. SOA, Safe Operation Area

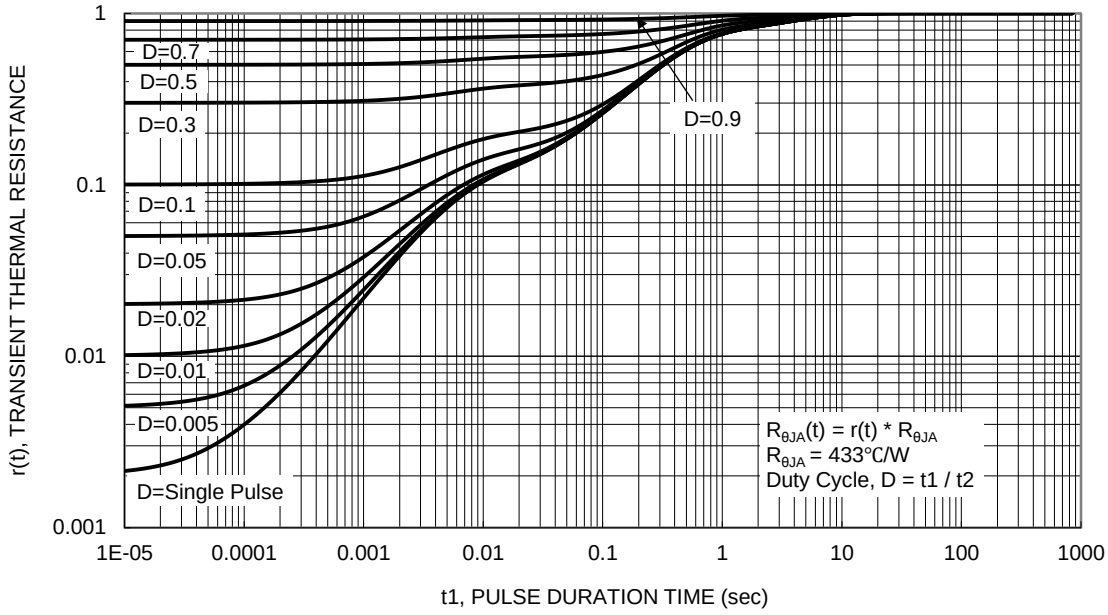
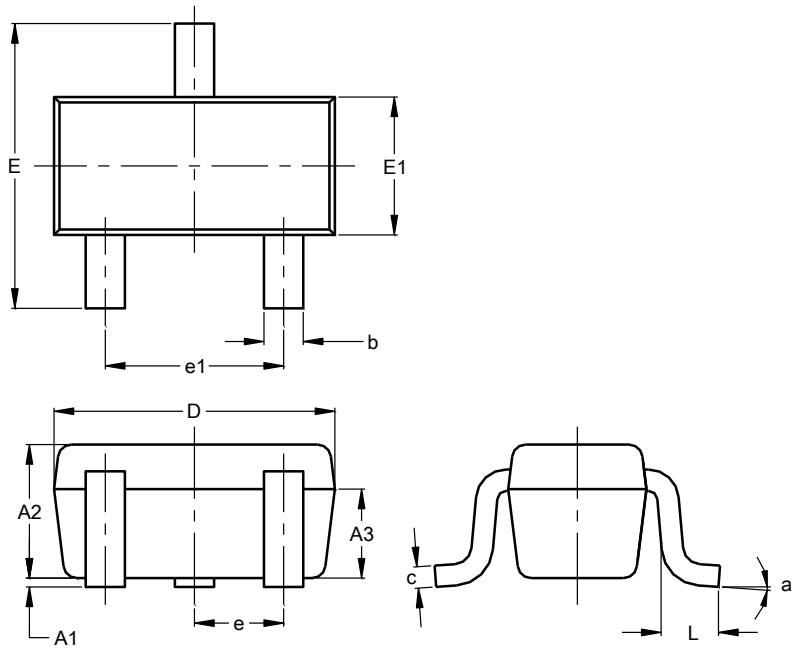


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

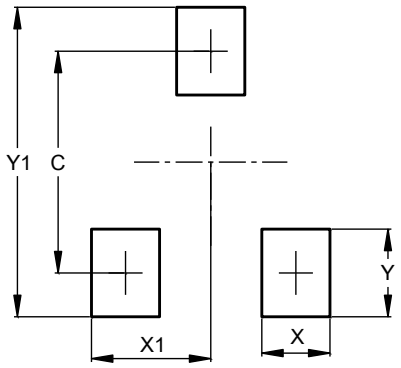


SOT523			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.60	0.80	0.75
A3	0.45	0.65	0.50
b	0.15	0.30	0.22
c	0.10	0.20	0.12
D	1.50	1.70	1.60
E	1.45	1.75	1.60
E1	0.75	0.85	0.80
e	0.50 BSC		
e1	0.90	1.10	1.00
L	0.20	0.40	0.33
a	0°	--	8°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)
C	1.29
X	0.40
X1	0.70
Y	0.51
Y1	1.80

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